

#### 2N4401

### **MMBT4401**





#### **NPN General Pupose Amplifier**

This device is designed for use as a medium power amplifier and switch requiring collector currents up to 500 mA.

#### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	6.0	V
I <sub>C</sub>	Collector Current - Continuous	600	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	М	Units	
		2N4401	*MMBT4401	
$P_{D}$	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# NPN General Purpose Amplifier (continued)

30

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Symbol	Parameter	Test Conditions	Min	Max	Units
055.0114	DA OTEDIOTION				
	RACTERISTICS		1	1	
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 0.1 \text{ mA}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 0.1 \text{ mA}, I_C = 0$	6.0		V
I <sub>BL</sub>	Base Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μА
I <sub>CEX</sub>	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, V_{EB} = 0.4 \text{ V}$		0.1	μА
ON CHAF	RACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$	20		
' 'FE	Do Guiterit Gairi	$I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40		
		$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	80		
		$I_C = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100	300	
		$I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$	40		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$		0.4	V
\ /	Door Emitter Caturation Valtage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	0.75	0.75 0.95	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	, 5	0.75		V
		$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.2	V
	IGNAL CHARACTERISTICS  Current Gain - Bandwidth Product	$I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$	250	1.2	MHz
f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz	250		MHz
$f_{T}$		$I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100  MHz $V_{CB} = 5.0 \text{ V}, I_{E} = 0,$	250	6.5	
	Current Gain - Bandwidth Product	$\begin{split} I_{C} &= 20 \text{ mA, } V_{CE} = 10 \text{ V,} \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \text{ V, } I_{E} = 0, \\ f &= 140 \text{ kHz} \\ V_{BE} &= 0.5 \text{ V, } I_{C} = 0, \end{split}$	250		MHz
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub>	Current Gain - Bandwidth Product  Collector-Base Capacitance	$\begin{split} I_{C} &= 20 \text{ mA, } V_{CE} = 10 \text{ V,} \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \text{ V, } I_{E} = 0, \\ f &= 140 \text{ kHz} \\ V_{BE} &= 0.5 \text{ V, } I_{C} = 0, \\ f &= 140 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V,} \end{split}$	250	6.5	MHz pF
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub>	Current Gain - Bandwidth Product  Collector-Base Capacitance  Emitter-Base Capacitance	$\begin{split} I_C &= 20 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 140 \text{ kHz} \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 140 \text{ kHz} \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_C &= 1.0 \text{ mA}, \ V_{CE} = 10 \text{ V}, \end{split}$		6.5	MHz pF pF kΩ
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub> h <sub>ie</sub>	Current Gain - Bandwidth Product  Collector-Base Capacitance  Emitter-Base Capacitance  Input Impedance	$\begin{split} I_C &= 20 \text{ mA, } V_{CE} = 10 \text{ V,} \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \text{ V, } I_E = 0, \\ f &= 140 \text{ kHz} \\ V_{BE} &= 0.5 \text{ V, } I_C = 0, \\ f &= 140 \text{ kHz} \\ I_C &= 1.0 \text{ mA, } V_{CE} = 10 \text{ V,} \\ f &= 1.0 \text{ kHz} \end{split}$	1.0	6.5 30 15	MHz pF pF kΩ
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub> h <sub>ie</sub> h <sub>re</sub>	Current Gain - Bandwidth Product  Collector-Base Capacitance  Emitter-Base Capacitance  Input Impedance  Voltage Feedback Ratio	$\begin{split} I_C &= 20 \text{ mA}, \ V_{CE} = 10 \ V, \\ f &= 100 \ MHz \\ V_{CB} &= 5.0 \ V, \ I_E = 0, \\ f &= 140 \ kHz \\ V_{BE} &= 0.5 \ V, \ I_C = 0, \\ f &= 140 \ kHz \\ I_C &= 1.0 \ mA, \ V_{CE} = 10 \ V, \\ f &= 1.0 \ kHz \\ I_C &= 1.0 \ mA, \ V_{CE} = 10 \ V, \\ f &= 1.0 \ kHz \\ I_C &= 1.0 \ mA, \ V_{CE} = 10 \ V, \end{split}$	1.0	6.5 30 15 8.0	MHz pF pF
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub> h <sub>ie</sub> h <sub>re</sub> h <sub>fe</sub>	Current Gain - Bandwidth Product  Collector-Base Capacitance  Emitter-Base Capacitance  Input Impedance  Voltage Feedback Ratio  Small-Signal Current Gain  Output Admittance	$\begin{split} I_C &= 20 \text{ mA}, \ V_{CE} = 10 \ V, \\ f &= 100 \ \text{MHz} \\ V_{CB} &= 5.0 \ \text{V}, \ I_E = 0, \\ f &= 140 \ \text{kHz} \\ V_{BE} &= 0.5 \ \text{V}, \ I_C = 0, \\ f &= 140 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ $	1.0 0.1 40	6.5 30 15 8.0 500	MHz pF pF kΩ x 10 <sup>-4</sup>
f <sub>T</sub> C <sub>cb</sub> C <sub>eb</sub> h <sub>ie</sub> h <sub>re</sub> h <sub>fe</sub> SWITCHI	Current Gain - Bandwidth Product  Collector-Base Capacitance  Emitter-Base Capacitance  Input Impedance  Voltage Feedback Ratio  Small-Signal Current Gain	$\begin{split} I_C &= 20 \text{ mA}, \ V_{CE} = 10 \ V, \\ f &= 100 \ \text{MHz} \\ V_{CB} &= 5.0 \ \text{V}, \ I_E = 0, \\ f &= 140 \ \text{kHz} \\ V_{BE} &= 0.5 \ \text{V}, \ I_C = 0, \\ f &= 140 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ f &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ \text{MA}, \ V_{CE} = 10 \ \text{V}, \\ I_C &= 1.0 \ $	1.0 0.1 40	6.5 30 15 8.0 500	MHz pF pF kΩ x 10 <sup>-4</sup>
f <sub>T</sub> Ccb Ceb h <sub>ie</sub> h <sub>re</sub> h <sub>fe</sub>	Current Gain - Bandwidth Product  Collector-Base Capacitance  Emitter-Base Capacitance  Input Impedance  Voltage Feedback Ratio  Small-Signal Current Gain  Output Admittance	$\begin{split} I_C &= 20 \text{ mA}, \ V_{CE} = 10 \ V, \\ f &= 100 \ \text{MHz} \\ V_{CB} &= 5.0 \ V, \ I_E = 0, \\ f &= 140 \ \text{kHz} \\ V_{BE} &= 0.5 \ V, \ I_C = 0, \\ f &= 140 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ f &= 1.0 \ \text{kHz} \\ I_C &= 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ f &= 1.0 \ \text{kHz} \\ \end{split}$	1.0 0.1 40	6.5 30 15 8.0 500 30	MHz pF pF kΩ x 10 <sup>-2</sup>

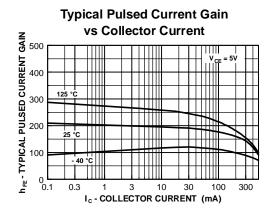
 $I_{B1} = I_{B2} = 15 \text{ mA}$ 

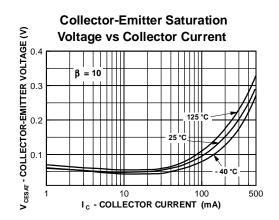
Fall Time

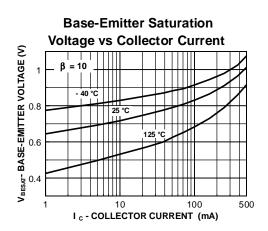
 $<sup>^\</sup>bigstar \text{Pulse Test: Pulse Width} \leq 300~\mu\text{s}, \, \text{Duty Cycle} \leq 2.0\%$ 

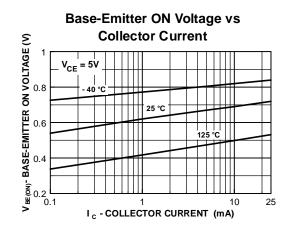
(continued)

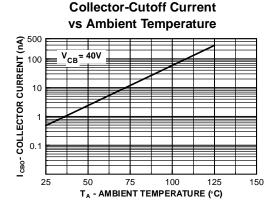
#### **Typical Characteristics**

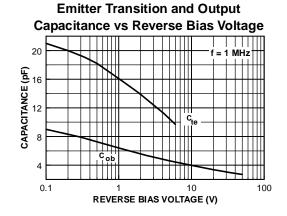








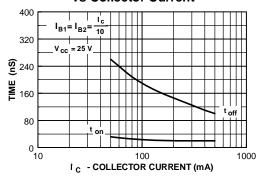




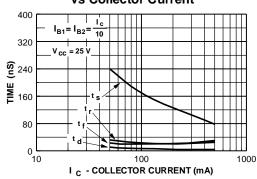
(continued)

#### Typical Characteristics (continued)

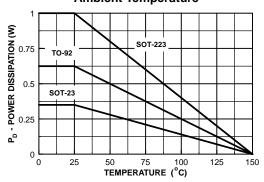
Turn On and Turn Off Times vs Collector Current



# Switching Times vs Collector Current

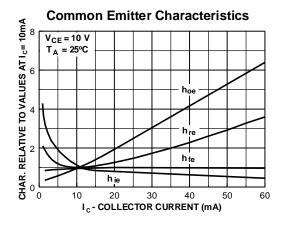


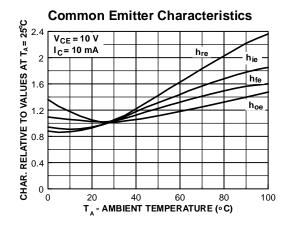
#### Power Dissipation vs Ambient Temperature

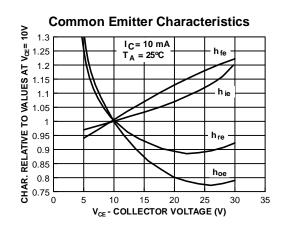


(continued)

#### **Typical Common Emitter Characteristics** (f = 1.0kHz)







(continued)

#### **Test Circuits**

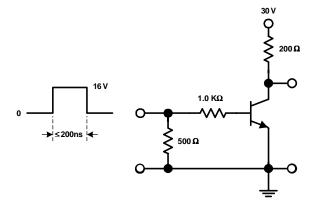


FIGURE 1: Saturated Turn-On Switching Timer

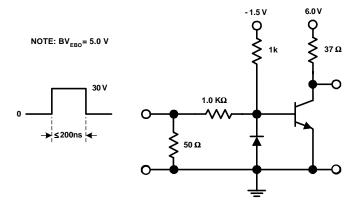


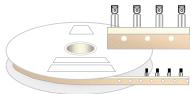
FIGURE 2: Saturated Turn-Off Switching Time

#### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

#### TO-92 Tape and Reel Data, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

#### Machine Option "A" (H)

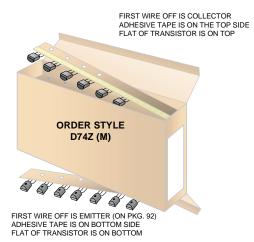


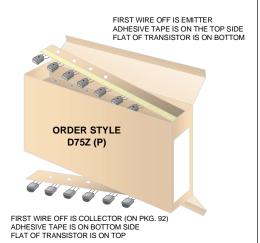
Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

# **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0



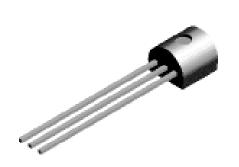


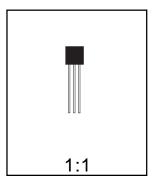


#### **TO-92 Package Dimensions**



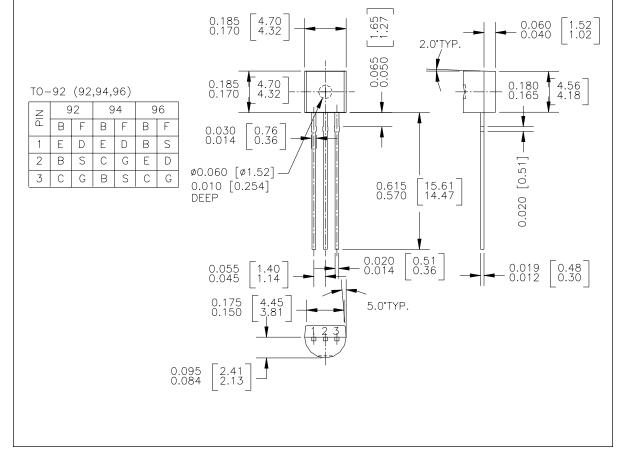
# TO-92 (FS PKG Code 92, 94, 96)

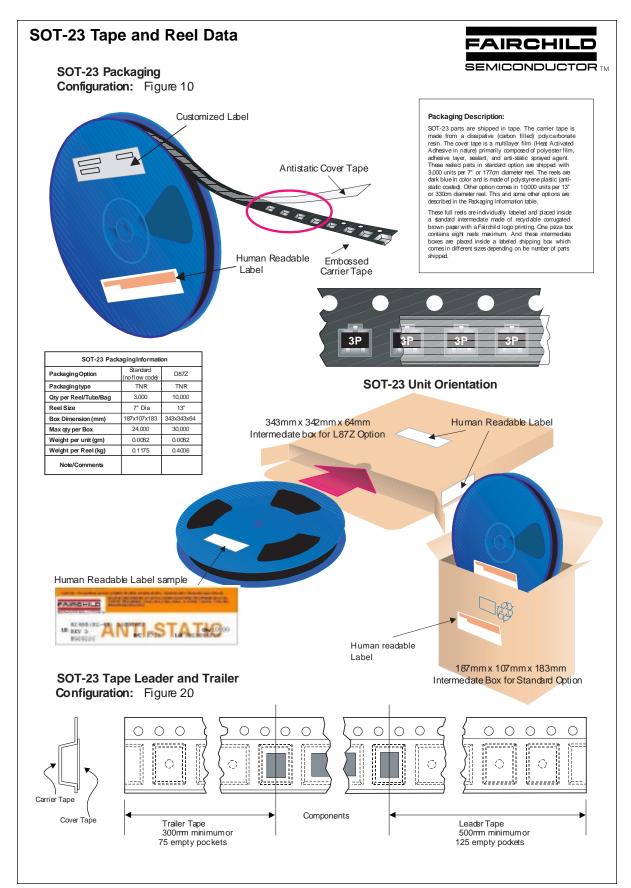




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

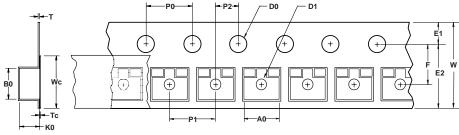




#### SOT-23 Tape and Reel Data, continued

#### **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0



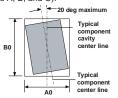
User Direction of Feed

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

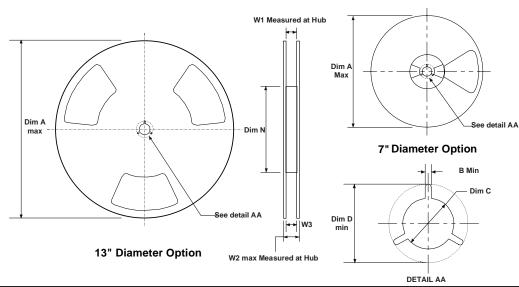


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

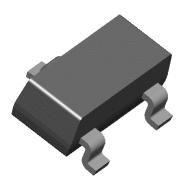
#### SOT-23 Reel Configuration: Figure 4.0

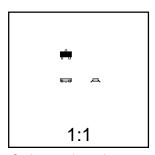


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



# SOT-23 (FS PKG Code 49)

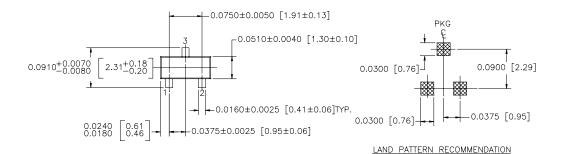


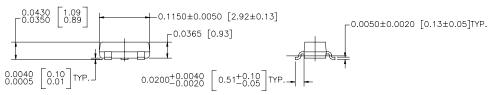


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





CONTROLLING DIMENSION IS INCH VALUES IN [ ] ARE MILLIMETERS SOT 23, 3 LEADS LOW PROFILE

NOTE : UNLESS OTHERWISE SPECIFIED

- STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition				
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